

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3338	PEO	USPAT	OR	OFF	2004/12/15 15:32
L2	274	PEOX	USPAT	OR	OFF	2004/12/15 15:34
L3	33	PEOX and (plasma adj enhanced) and oxygen	USPAT	OR	OFF	2004/12/15 15:39
S1	569	(438/758).CCLS.	USPAT	OR	OFF	2004/12/15 13:10
S2	73	S1 and polysilicon and gate	USPAT	OR	OFF	2004/12/15 13:10
S3	1	S1 and polysilicon and gate and wafer and dope	USPAT	OR	OFF	2004/12/15 13:10
S4	31	S1 and polysilicon and gate and wafer and nitrogen	USPAT	OR	OFF	2004/12/15 13:10
S5	5	S1 and polysilicon and gate and wafer and (nitrogen with doped)	USPAT	OR	OFF	2004/12/15 13:10
S6	3	S1 and polysilicon and gate and wafer and (nitrogen with doped) and mask	USPAT	OR	OFF	2004/12/15 13:11
S7	8	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:45
S8	0	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO and (phosphoric adj acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:45
S9	5	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO and wet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 15:32
S10	0	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO and PEOX	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:54
S11	2	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO and SiON	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:56

S12	3	(plasma-enhanced) and (polysilicon) and mask and (wet adj etch) and RTO and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:57
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